		40553054					
Application Number:	10:	10563854					
Filing Date:	09-	09-Jun-2006					
Title of Invention:	GR	GROWTH METHOD FOR NITRIDE SEMICONDUCTOR EPITAXIAL LAYERS					
First Named Inventor/Applicant Name:	Eui	Euijoon Yoon					
Filer:	Sar	Samuel Digirolamo/Lisa Lilburn					
Attorney Docket Number:	50-	504478.24					
Filed as Large Entity							
U.S. National Stage under 35 USC 371 I	Filing Fee	5					
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)		
Basic Filing:							
Pages:							
Claims:							
Miscellaneous-Filing:							
Petition:							
Patent-Appeals-and-Interference:							
Post-Allowance-and-Post-Issuance:							

Publ. Fee- early, voluntary, or normal

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension-of-Time:				
Miscellaneous:				
	Total in USD (\$)			1810